



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SS82C-SS810C

SMC Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■ Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMC(DO-214AB)



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS 82C	SS 83C	SS 84C	SS 85C	SS 86C	SS 88C	SS 89C	SS 810C	Unit 单位
Marking 印字		SS82	SS83	SS84	SS85	SS86	SS88	SS89	SS810	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	50	60	80	90	100	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	50	60	80	90	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	35	42	56	63	70	V
Forward Rectified Current 正向整流电流	I_F	8								A
Peak Surge Current 峰值浪涌电流	I_{FSM}	175								A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	10								$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150								$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-65to+150 $^{\circ}\text{C}$								$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS82C-SS84C	SS85C-SS86C	SS88C-SS810C	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.55	0.70	0.85	V	$I_F=8\text{A}$
Reverse Current 反向电流	$I_R(25^{\circ}\text{C})$ (100°C)	0.1 5		0.02 2	mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	380			pF	$V_R=4\text{V}$, $f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

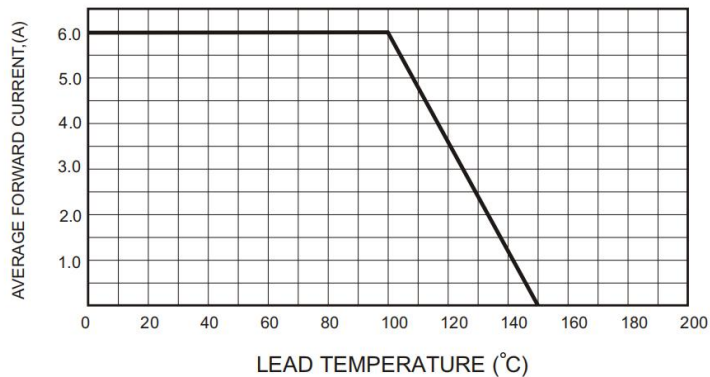


Fig.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

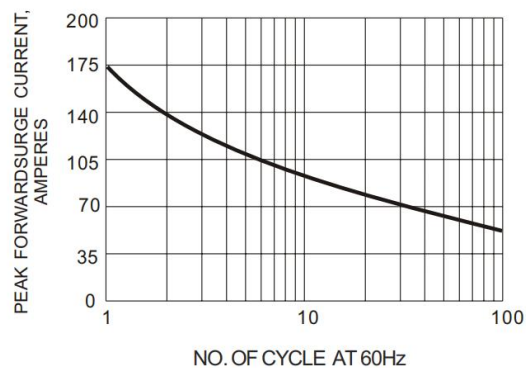


FIG.3-TYPICAL FORWARD CHARACTERISTICS

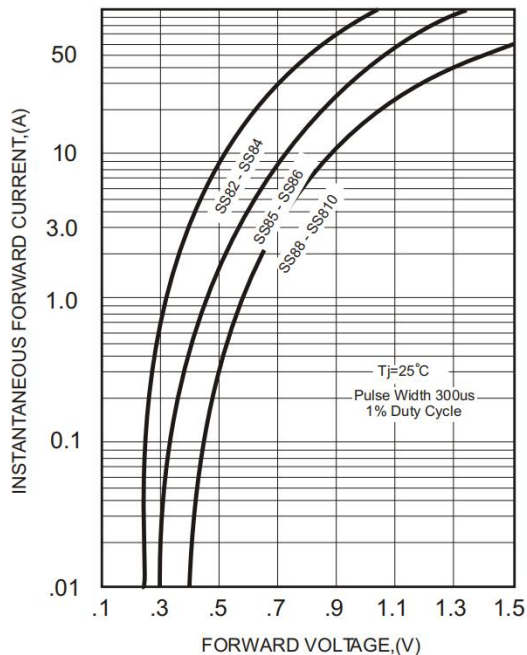
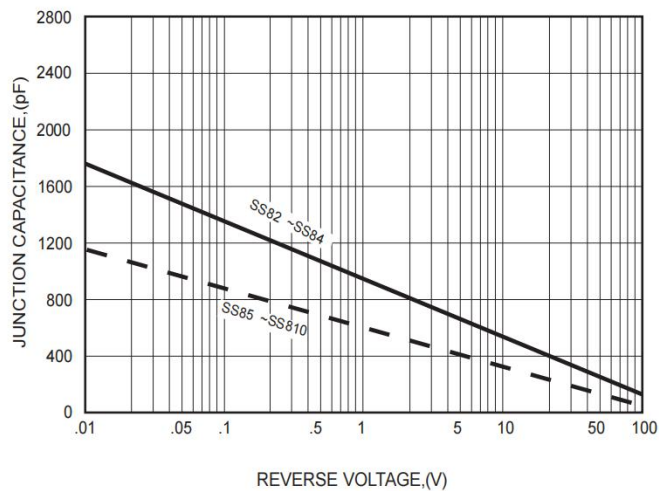
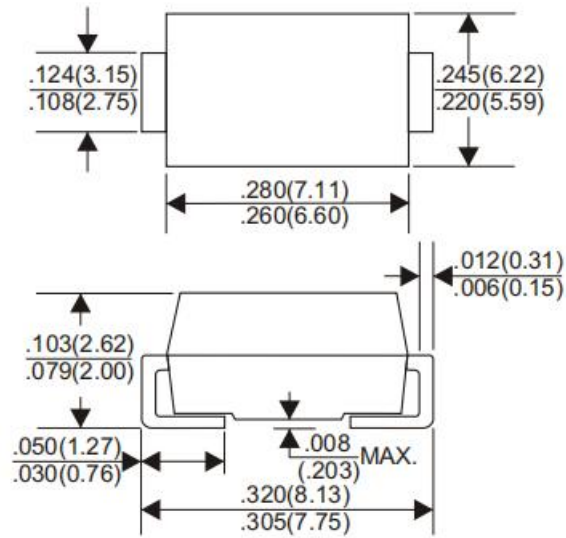


FIG.4-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AB(SMC)



Dimensions in inches and (millimeters)